

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	11301	select\$3 adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:01
S2	14149	select\$3 adj transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:01
S3	31228	floating adj gate\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:01
S4	102	byte adj2 transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:02
S5	840	word adj2 transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:02
S6	8497	first adj width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:02
S7	7356	second adj width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:03
S8	120514	gate adj (oxide or insulat\$3 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:04
S9	1336	polysi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:04
S10	120720	polysi\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:07

S11	63304	polycrystal\$4 adj (Si or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:14
S12	11241	first adj (S9 or S10 or S11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:16
S13	10986	second adj (S9 or S10 or S11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:16
S14	251764	multi\$1layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:16
S15	0	(S1 or S2) and S3 and (S4 or S5) and (S6 same S7 same S8 same S12 same S13 same S14)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:20
S16	0	(S1 or S2) and S3 and (S4 or S5) and (S6 same S7 same S14)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:21
S17	165	(S1 or S2) and S3 and (S4 or S5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/15 18:21